

FEATURES

- Circular Active Area
- Ideal for EUV Detection
- 100% Internal Quantum Efficiency
- High Speed
- Grid Lines 5 microns, Pitch 100 microns
- Superior Radiation Hardness
- High Photon Flux Robustness
- TO-8 Package

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	Ø5.01mm		20		mm ²
Responsivity, \mathcal{R}	(see graph on next page)				A/W
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$	160			Volts
Capacitance, C	$V_R = 0V$		200	800	pF
Rise Time	$R_L = 50\Omega, V_R = 150V$			2	nsec
Dark Current	$V_R = 150V$			100	nA

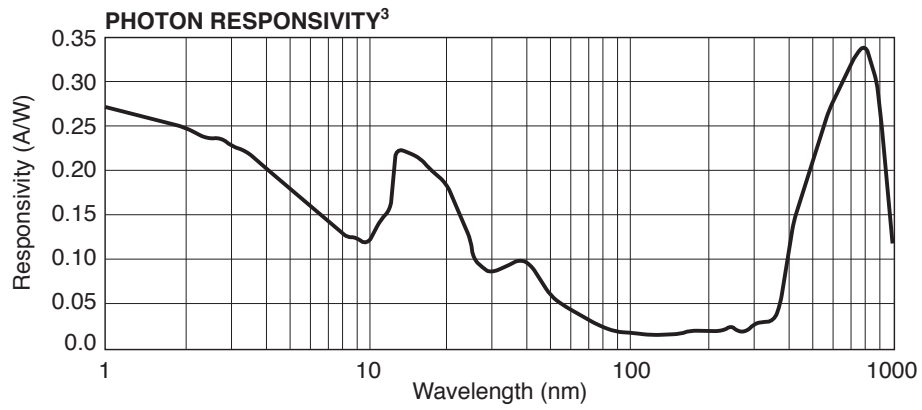
THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient ¹	-10° TO 40°C ²
Nitrogen or Vacuum	-20°C TO 80°C
Lead Soldering Temperature ²	260°C

¹Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

²0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.



³Between grid lines, overall responsivity for large spot sizes will be less.

Ordering Information

SXUV20HS1 ODD-SXU-004 High Speed EUV Detector in TO8 Package